FIG.1

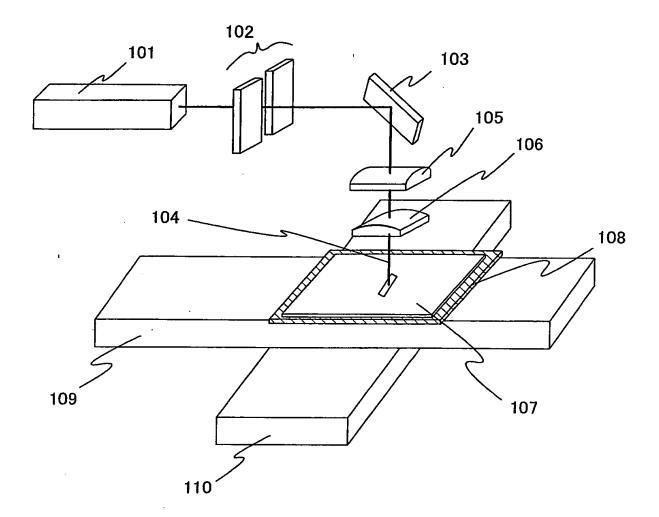


FIG.2A

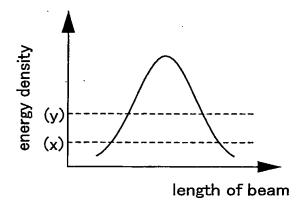


FIG.2B

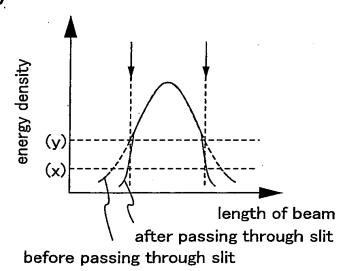


FIG.3

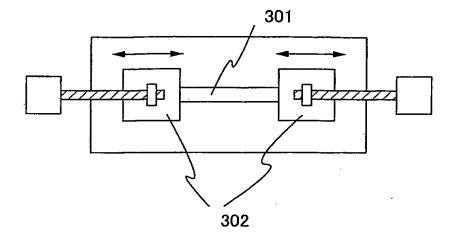
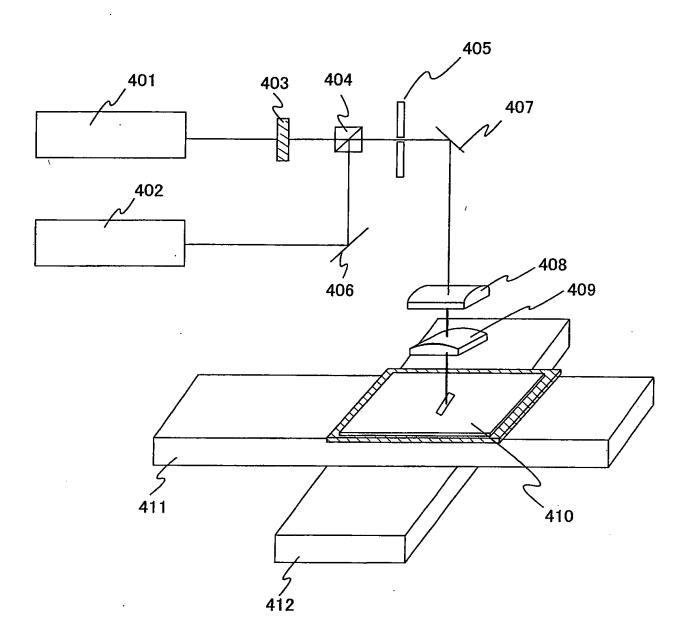


FIG.4



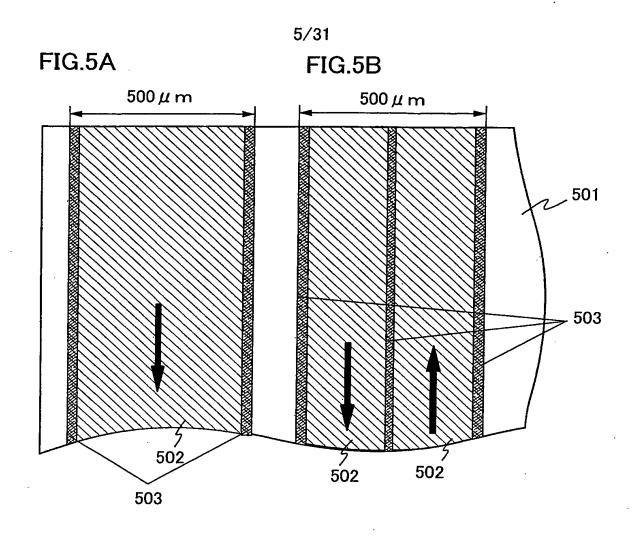
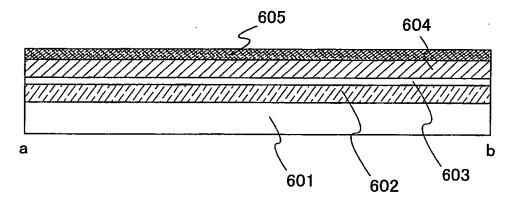
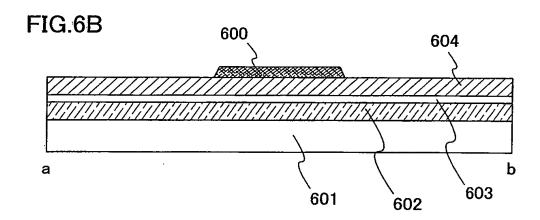
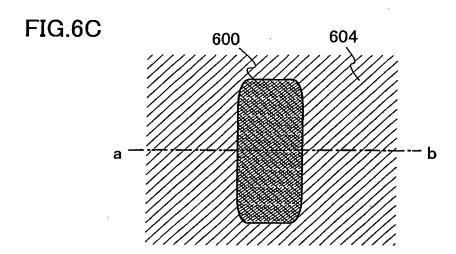


FIG.6A







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FIG.7A

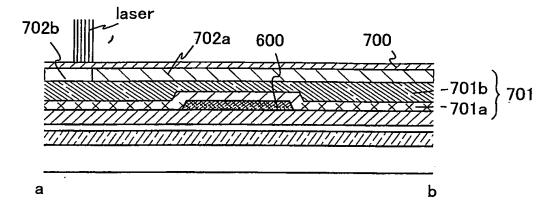


FIG.7B

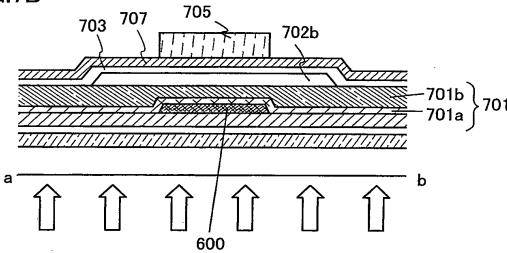


FIG.7C

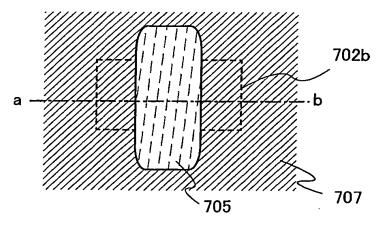
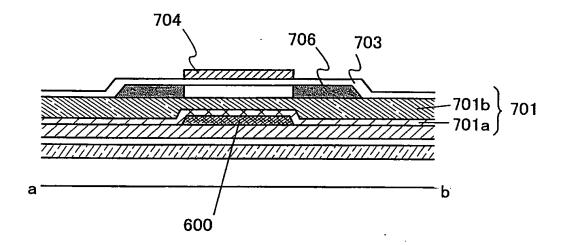
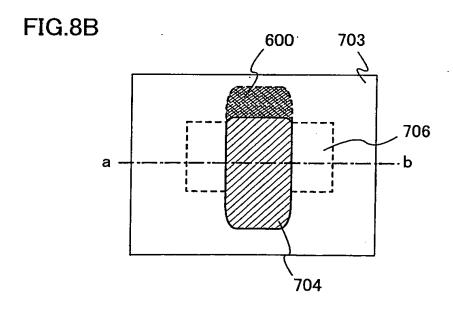


FIG.8A





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FIG.9A

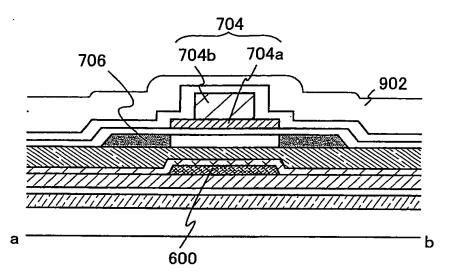


FIG.9B

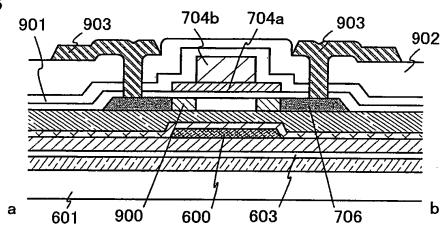
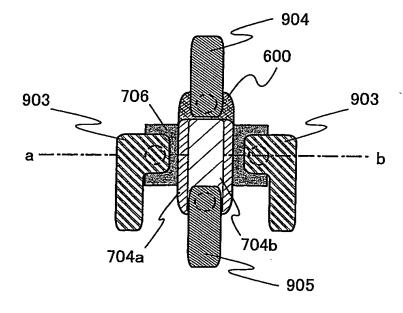
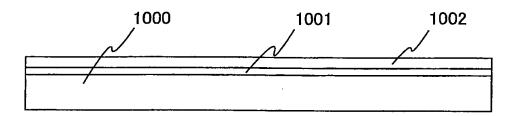


FIG.9C



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FIG.10A



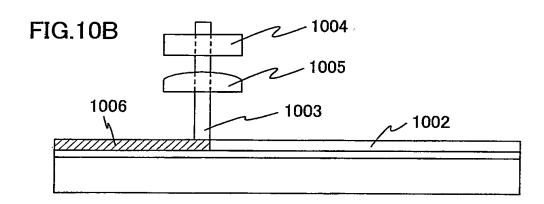
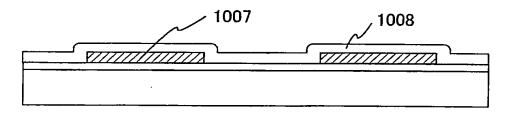
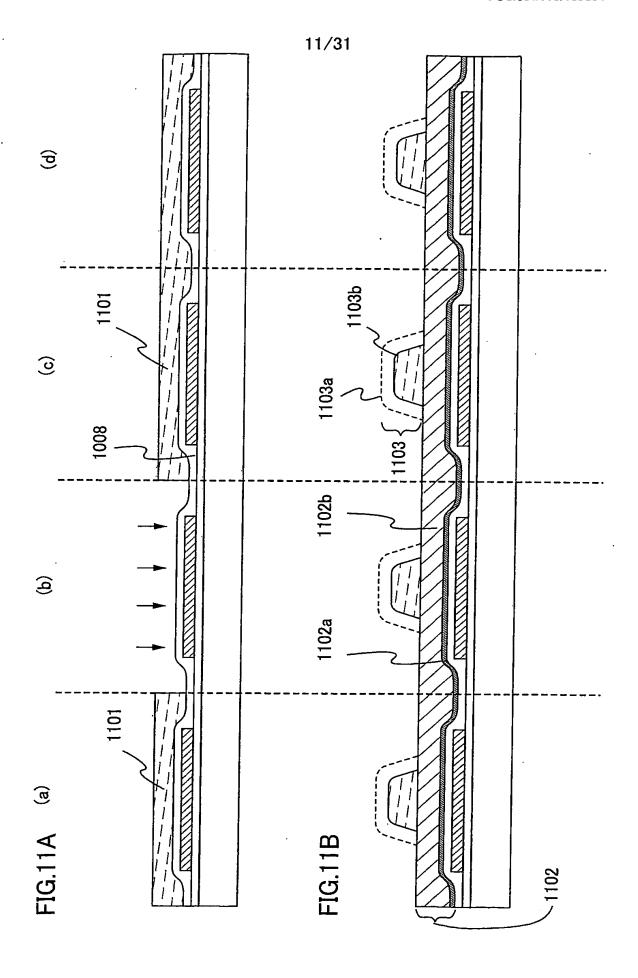
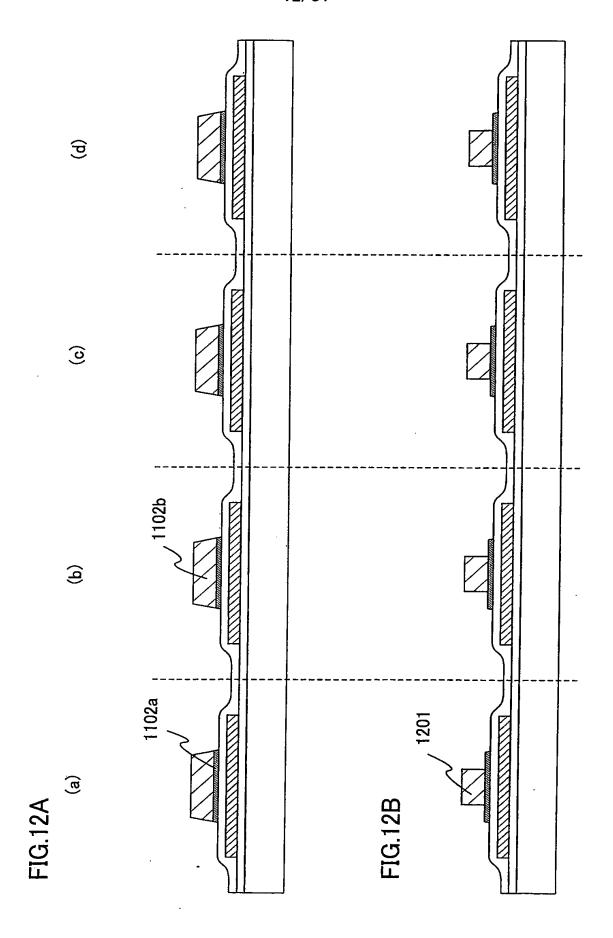


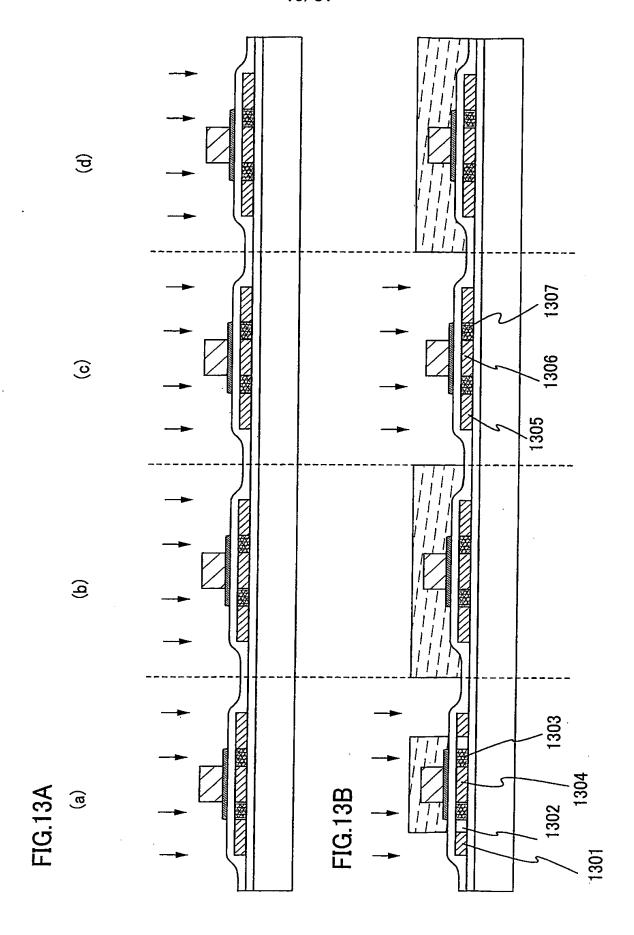
FIG.10C

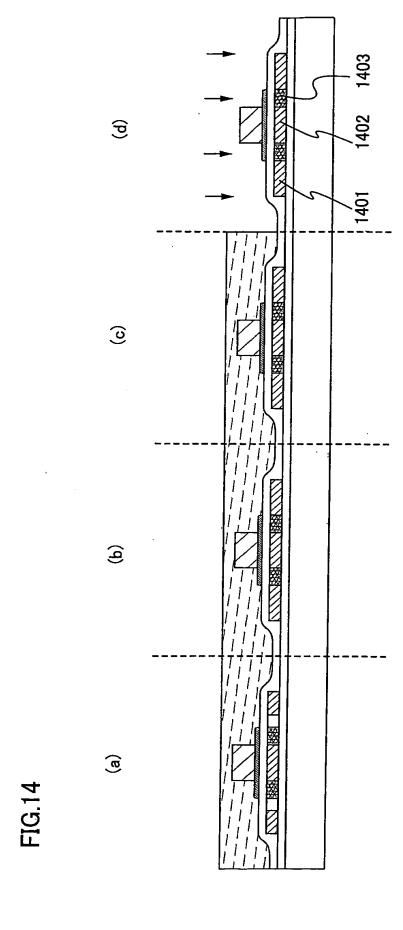


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FIG.15A

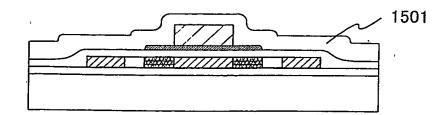


FIG.15B

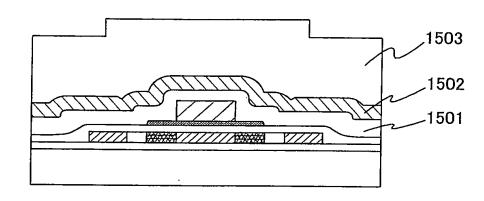


FIG.15C

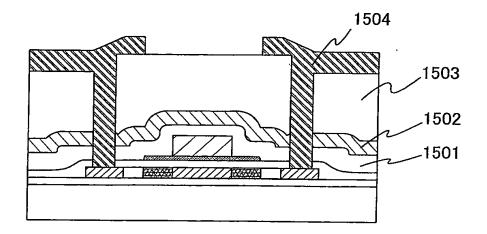




FIG.16A

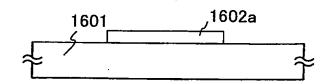


FIG.16B

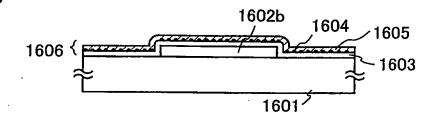


FIG.16C

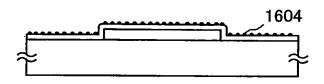


FIG.16D

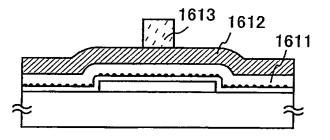


FIG.16E

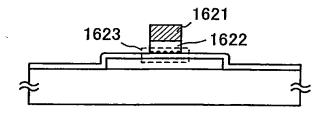


FIG.16F

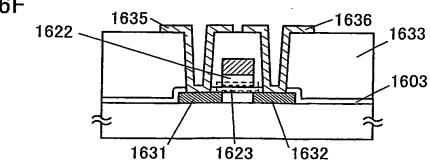


FIG.17A

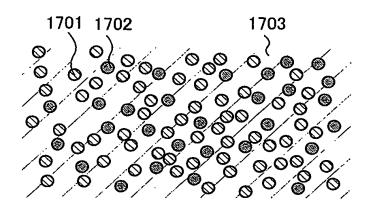


FIG.17B

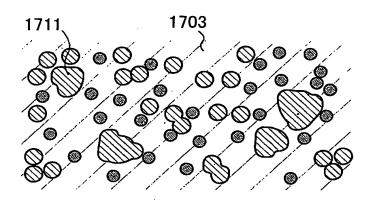


FIG.17C

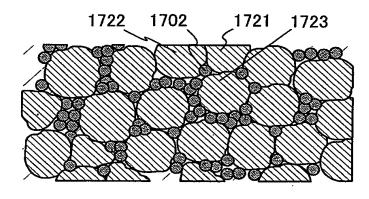


FIG.17D

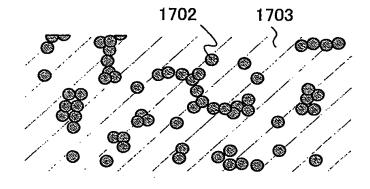
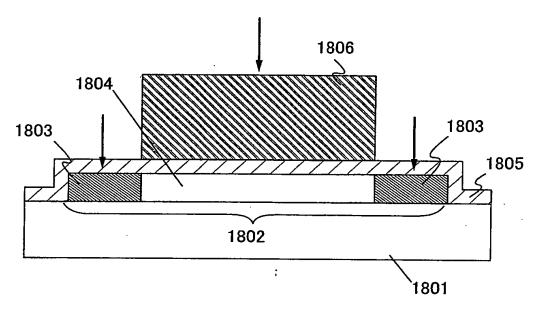
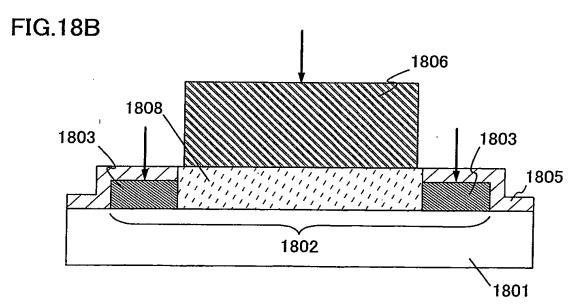


FIG.18A







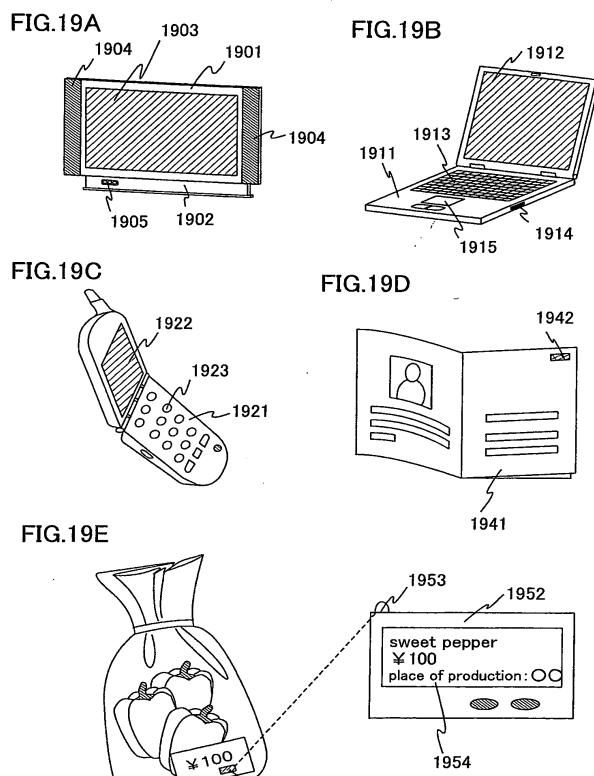
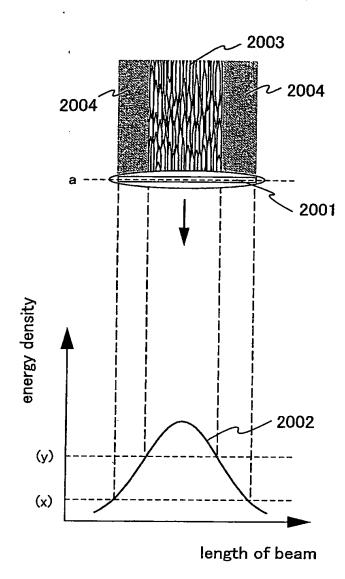


FIG.20



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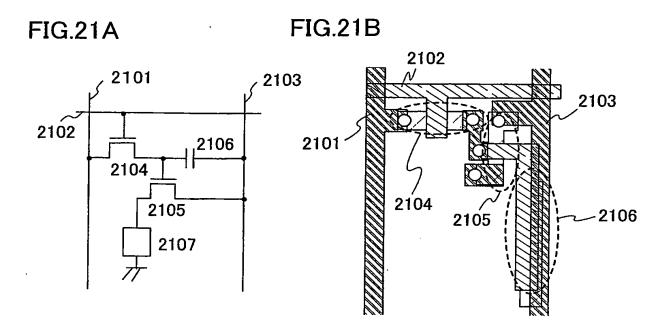
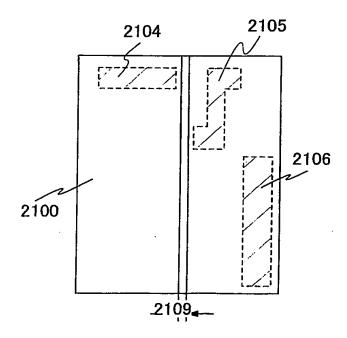


FIG.21C



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FIG.22

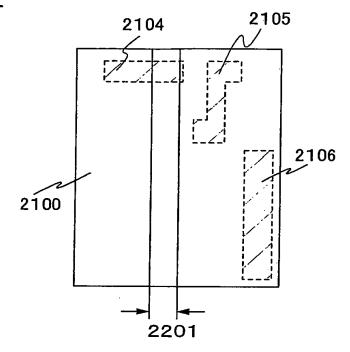


FIG.23

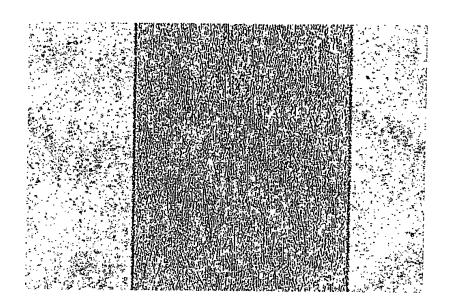
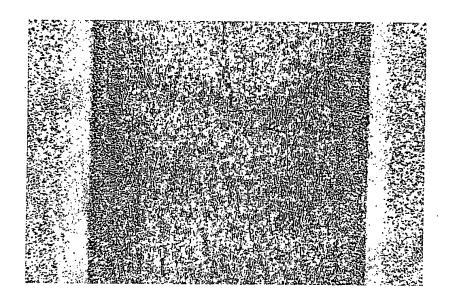
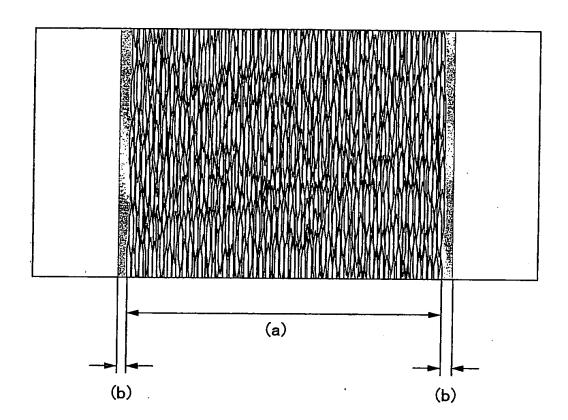


FIG.24



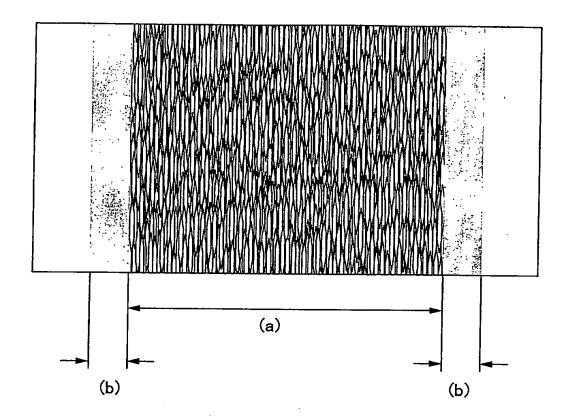
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FIG.25



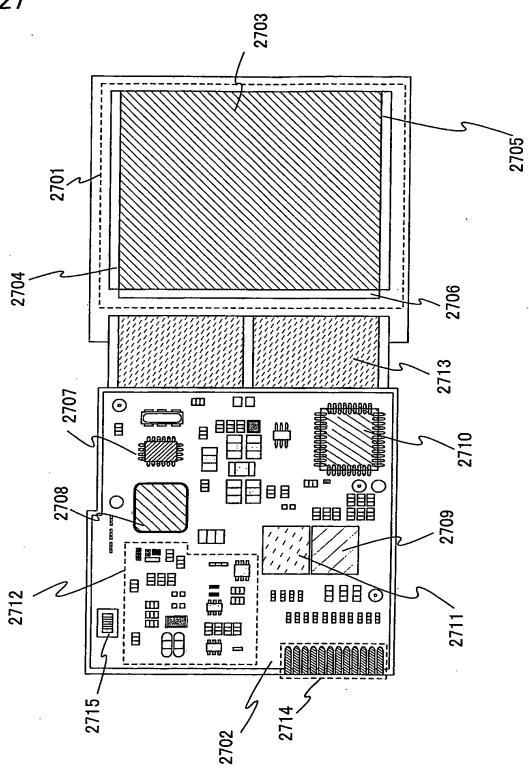
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FIG.26



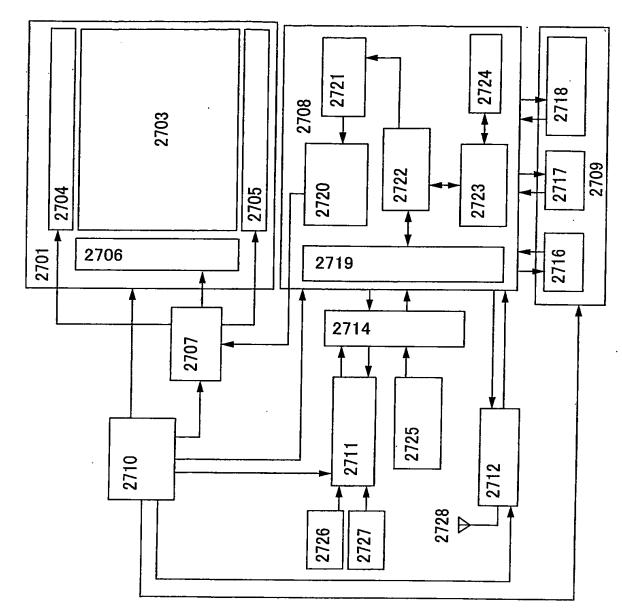
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FIG.27



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FIG.28



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EXPLANATION OF REFERENCE

101: LASER OSCILLATOR, 102: SLIT, 103: MIRROR, 104: BEAM, 105: CONVEX CYLINDRICAL LENS, 106: CONVEX CYLINDRICAL LENS, 107: SUBSTRATE, 108: SUCTION STAGE, 109: X STAGE, 110: Y STAGE, 301: SLIT OPENING PORTION, 302: BLOCKING PLATE, 401: LASER, 402: LASER, 403: HALF-WAVEPLATE, 404: POLARIZING BEAM SPLITTER, 405: SLIT, 406: MIRROR, 407: MIRROR, 408: CONVEX CYLINDRICAL LENS, 409: CONVEX CYLINDRICAL LENS, 410: SEMICONDUCTOR FILM, 411: X STAGE, 412: Y STAGE, 501: SEMICONDUCTOR FILM, 502: LARGE CRYSTAL GRAIN REGION, 600: LOWER ELECTRODE, 601: FIRST SUBSTRATE, 602: METAL FILM, 603: METAL OXIDE FILM, 604: SILICON OXIDE FILM, 605: CONDUCTIVE FILM, 700: INSULATING FILM, 701: FIRST GATE INSULATING FILM, 701a: SILICON NITRIDE OXIDE FILM, 701b: SILICON OXYNITRIDE FILM, 702a: NON-SINGLE CRYSTAL SEMICONDUCTOR FILM, 702b: CRYSTALLINE SEMICONDUCTOR FILM, 703: SECOND GATE INSULATING FILM, 704: UPPER ELECTRODE, 704a: CONDUCTIVE FILM, 704b: CONDUCTIVE FILM, 705: RESIST MASK, 706: IMPURITY REGION, 707: SECOND CONDUCTIVE FILM, 900: LDD REGION, 901: INSULATING FILM, 902: INTERLAYER INSULATING FILM, 903: WIRING, 1000: SUBSTRATE, 1001: BASE FILM, 1002: NON-SINGLE CRYSTAL SEMICONDUCTOR FILM, 1003: LASER, 1004: CYLINDRICAL LENS, 1005: CYLINDRICAL LENS, 1006: CRYSTALLINE SEMICONDUCTOR FILM, 1007: SEMICONDUCTOR FILM, 1008: GATE INSULATING FILM, 1101: RESIST, 1102: CONDUCTIVE FILM, 1102a: FIRST CONDUCTIVE FILM, 1103: RESIST MASK,

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1103a: RESIST MASK, 1003b: RESIST MASK, 1201: GATE ELECTRODE, 1301: SOURCE REGION, 1302: LOW-CONCENTRATION IMPURITY REGION, 1303: REGION WHERE LOW-CONCENTRAION IMPURITY REGION OVERLAPS TaN OF GATE ELECTRODE, 1304: CHANNEL REGION, 1305: DRAIN REGION, 1306: CHANNEL REGION, 1307: REGION OVERLAPPING TaN OF GATE ELECTRODE, 1401: SOURCE REGION AND DRAIN REGION, 1402: CHANNEL REGION, 1403: REGION OVERLAPPING TaN OF GATE ELECTRODE, 1501: CAP OXIDE FILM, 1502: INSULATING FILM, 1503: INSULATING FILM, 1504: WIRING, 1601: NON-SINGLE CRYSTAL SEMICONDUCTOR FILM, 1602a: NON-SINGLE CRSYTAL SEMICONDUCTOR FILM, 1602b: CRYSTALLINE SEMICONDUCTOR FILM, 1603: FIRST INSULATING FILM, 1604: MICROPARTICLE OF SILICON CRYSTAL, 1605: CONDUCTIVE FILM, 1606: FIRST CONDUCTIVE FILM, 1611: SECOND CONDUCTIVE FILM, 1612: SECOND CONDUCTIVE FILM, 1613: MASK PATTERN, 1621: GATE ELECTRODE, 1622: SECOND INSULATING LAYER, 1623: FLOATING GATE ELECTRODE, 1631: SOURCE REGION, 1632: DRAIN REGION, 1633: THIRD INSULATING FILM, 1634: FIRST INSULATING FILM, 1635: SOURCE ELECTRODE, 1636: DRAIN ELECTRODE, 1701: PARTICLE CONTAINING METAL ELEMENT, 1702: MICROPARTICLE CONTAINING SILICON CRYSTAL, 1703: SUBSTRATE, 1711: PARTICLE CONTAINING METAL ELEMENT, 1721: PARTICLE CONTAINING METAL ELEMENT, 1722: PARTICLE CONTAINING METAL ELEMENT, 1723: PARTICLE CONTAINING METAL ELEMENT, 1801: INSULATING SUBSTRATE, 1802: SEMICONDUCTOR FILM, 1803: HIGH-CONCENTRATION IMPURITY ELEMENT, 1804: CHANNEL REGION, 1805: GATE INSULATING FILM, 1806: GATE ELECTRODE, 1808:

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INSULATED REGION, 1901: CASE, 1902: SUPPORTING STAND, 1903: DISPLAY PORTION, 1904: SPEAKER PORTION, 1905: VIDEO INPUT TERMINAL, 1911: CASE, 1912: DISPLAY PORTION, 1913: KEYBOARD, 1914: EXTERNAL CONNECTION PORT, 1915: POINTING MOUSE, 1921: CASE, 1922: DISPLAY PORTION, 1923: OPERATION KEY, 1941: PASSPORT, 1942: RADIO FREQUENCY IC TAG, 1951: RADIO FREQUENCY IC TAG, 1952: READER, 1953: ANTENNA PORTION, 2001: BEAM SPOT, 2002: ENERGY DENSITY DISTRIBUTION, 2003: CENTRAL REGION OF BEAM SPOT, 2004: END PORTION OF BEAM SPOT, 2100: SEMICONDUCTOR FILM, 2101: SOURCE SIGNAL LINE, 2102: GATE SIGNAL LINE, 2103: CURRENT SUPPLYING LINE, 2104: SWITCHING TFT, 2105: DRIVER TFT, 2106: CAPACITOR, 2107: LIGHT-EMITTING ELEMENT, 2109: MICROCRYSTAL REGION, 2201: MICROCRYSTAL REGION, 2701: DISPLAY PANEL, 2702: PRINT SUBSTRATE, 2703: PIXEL PORTION, 2704: FIRST SCANNING LINE DRIVER CIRCUIT, 2705: SECOND SCANNING LINE DRIVER CIRCUIT, 2706: SIGNAL LINE DRIVER CIRCUIT, 2707: CONTROLLER, 2708: CENTRAL PROCESSING UNIT, 2709: MEMORY, 2710: POWER SUPPLY CIRCUIT, 2711: AUDIO PROCESSING CIRCUIT, 2712: SENDING/RECEIVING CIRCUIT, 2713: FLEXIBLE WIRING SUBSTRATE, 2714: INTERFACE (I/F) PORTION, 2715: ANTENNA PORT, 2716: VRAM, 2717: DRAM, 2718: FLASH MEMORY, 2719: INTERFACE, 2720: CONTROL SIGNAL GENERATING CIRCUIT, 2721: DECODER, 2722: RESISTOR, 2723: ARITHMETIC CIRCUIT, 2724:VRAM, 2725: INPUT MEANS, 2726: MICROPHONE, 2727: SPEAKER, 2728: ANTENNA